

PATENT ABSTRACTS OF JAPAN

(11) Publication number : 64-009897
(43) Date of publication of application : 13.01.1989

31

(51) Int.Cl. C30B 29/40
C30B 25/14
// H01L 21/205

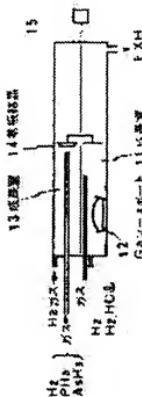
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(54) METHOD FOR GROWING III-V COMPOUND SEMICONDUCTOR CRYSTAL ON SI SUBSTRATE

(57) Abstract:

PURPOSE: To grow the titled superconductor crystal, having good crystallinity and capable of selective growth on a substrate, by alternately feeding a gas species containing a group III constituent element and a gas species containing a group V constituent element onto a silicon substrate having a formed mask pattern.

CONSTITUTION: A source boat 12 of a group III constituent element is placed on the upstream side of a growth chamber 11 in the lower stage and a carrier gas and HCl gas are fed from the upstream side thereof to adsorb the formed chloride of the group III constituent element on a silicon substrate 14 having a formed mask pattern. The substrate 14 is then moved to a growth chamber 13 in the upper stage and a gas species containing a group V constituent element is fed and adsorbed on the substrate 14. The above-mentioned operations are alternately repeated to carry out atomic layer epitaxial growth of a III-V compound semiconductor crystal on the substrate 14.



LEGAL STATUS

- [Date of request for examination]
- [Date of sending the examiner's decision of rejection]
- [Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]
- [Date of final disposal for application]
- [Patent number]
- [Date of registration]
- [Number of appeal against examiner's decision of rejection]
- [Date of requesting appeal against examiner's decision of rejection]
- [Date of extinction of right]